

Abstract

A method for producing a semiconductor device comprises forming an opening by etching process using a resist pattern as a 5 mask in a multi-layered film having a first organic insulating film, a first etching stop film and a second organic insulating film being layered in this order such that the opening penetrates from the first organic insulating film to the second organic insulating film, wherein a second etching stop film is formed between the resist pattern and the 10 second organic insulating film to protect the second organic insulating film from being etched during the formation of the opening.